

Released

X-band Radar Front End

Model No. NJT1949A

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Microwave Business Headquarters**

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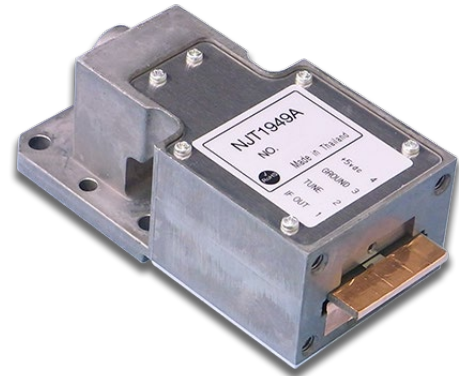
■ GENERAL DESCRIPTION

NJT1949A is designed for the front end of marine radar system.

It features a small size and a light weight operable at any frequency between 9.415GHz and 9.475GHz.

This front end module consists of GaAs FET low noise amplifier, Image rejection mixer, Local VCO with buffer amplifier.

The stability of the local VCO frequency by the input RF power is increased effectively by the buffer amplifier which is located between image rejection mixer and local VCO.



■ ELECTRICAL CHARACTERISTICS < at 25 °C >

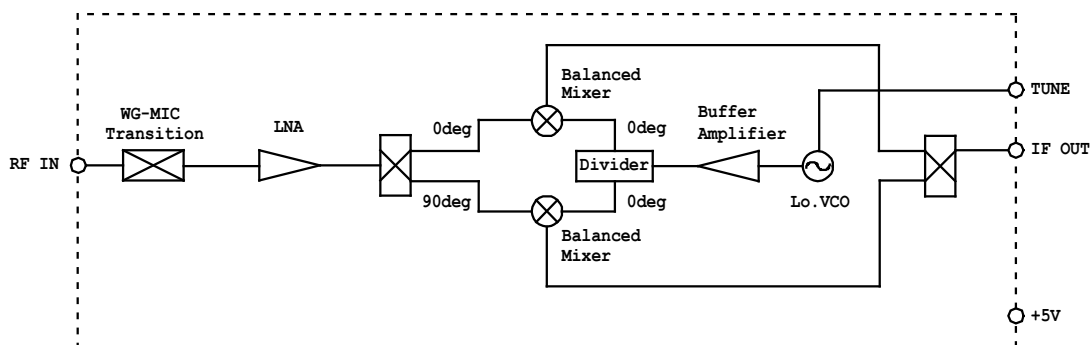
PARAMETERS		MINIMUM	TYPICAL	MAXIMUM	UNITS
Operating voltage		4.8	5.0	5.2	V
Operating current		-	70	90	mA
Tuning Voltage	(Note1)	12.5	14.5	16.5	V
Local frequency	VT= 6V	-	-	9.445	GHz
	VT=24V	9.565	-	-	GHz
Noise figure		-	3.0	3.5	dB
Conversion gain		3.0	6.0	-	dB
RF single pulse burnout	(Note2)	-	-	600	mW
RF repetitive pulse burnout	(Note3)	-	-	400	mW

Note1: fLO=9.505GHz

Note2: fRF=9.445GHz, Pd=10nsec

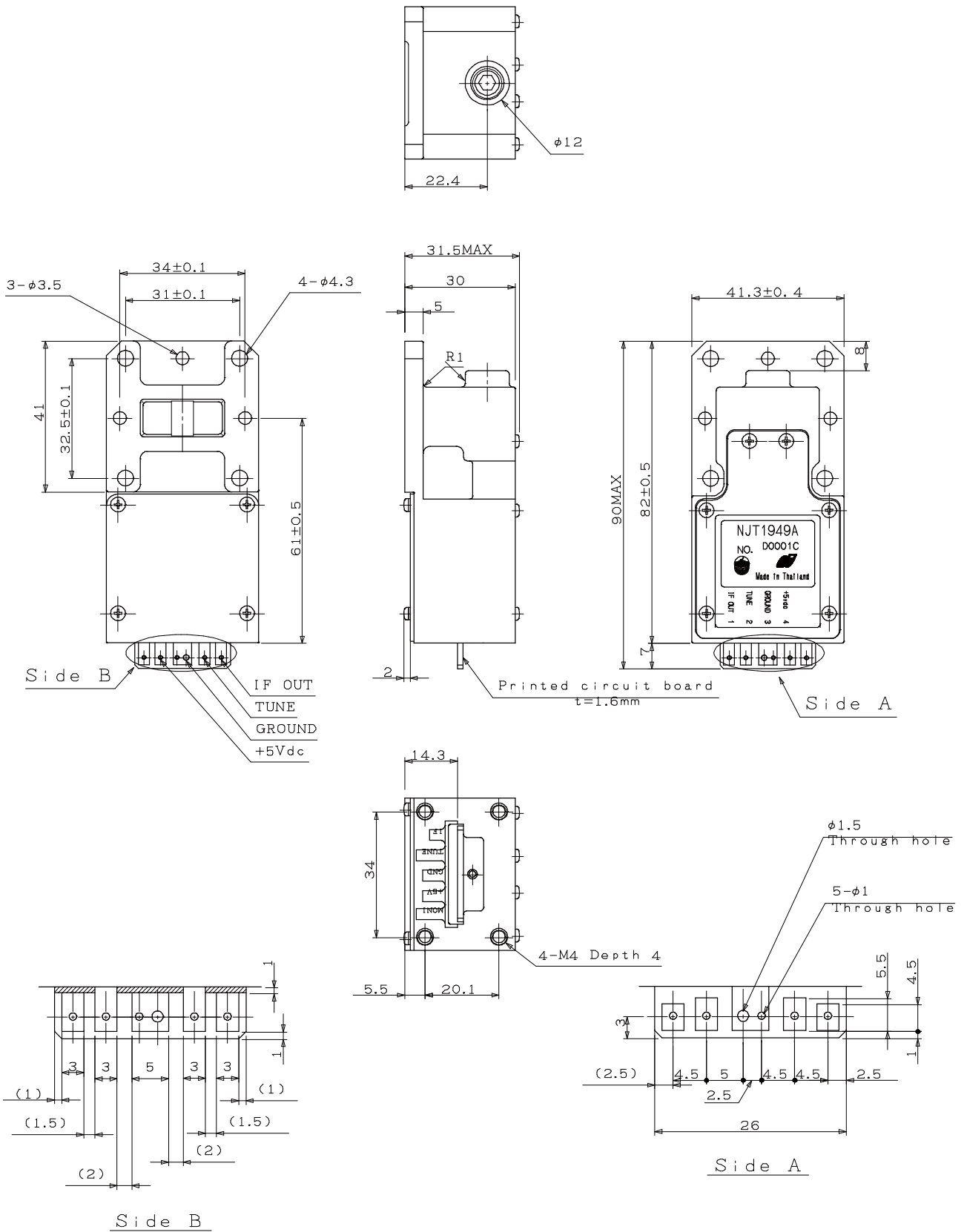
Note3: fRF=9.445GHz, Pd=1µsec, Duty=0.001

■ BLOCK DIAGRAM



* Above Specifications are subject to change without notice.

■ OUTLINE



(Dimensions are expressed in "mm".)

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